BTA208X-800E



3Q Hi-Com Triac Rev. 07 — 25 January 2011

Product data sheet

1. **Product profile**

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series E" is intended for interfacing with low power drivers including microcontrollers.

1.2 Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

Electronic thermostats

General purpose motor controls

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5	-	-	65	Α
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 73$ °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	8	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G -;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;} $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ Composition}}$	-	-	10	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N .
2	T2	main terminal 2	mb	T2 — T1
3	G	gate		sym051
mb	n.c.	mounting base; isolated		
			SOT186A (TO-220F)	

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BTA208X-800E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 73$ °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	8	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	65	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	71	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	21	A^2s
dI _T /dt	rate of rise of on-state current	$I_T = 0.2 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	2	Α
V_{GM}	peak gate voltage		-	5	V
P _{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

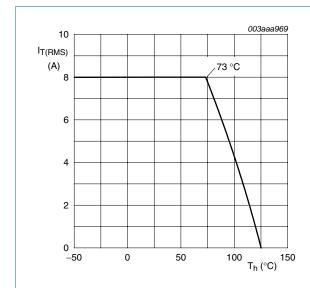
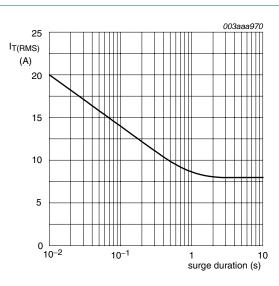


Fig 1. RMS on-state current as a function of heatsink temperature; maximum values



 $f = 50 \text{ Hz}; T_h = 73 \,^{\circ}C$

Fig 2. RMS on-state current as a function of surge duration; maximum values

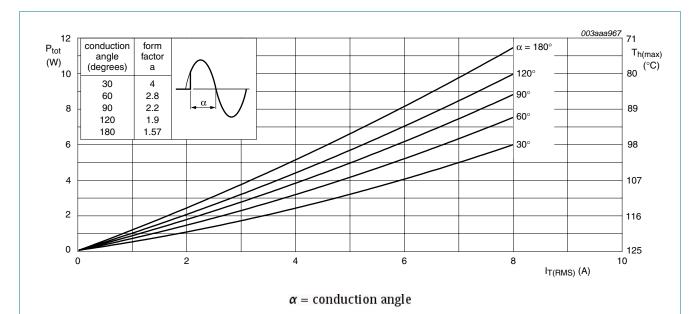


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

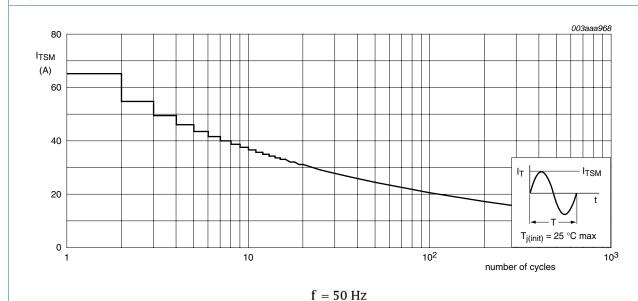
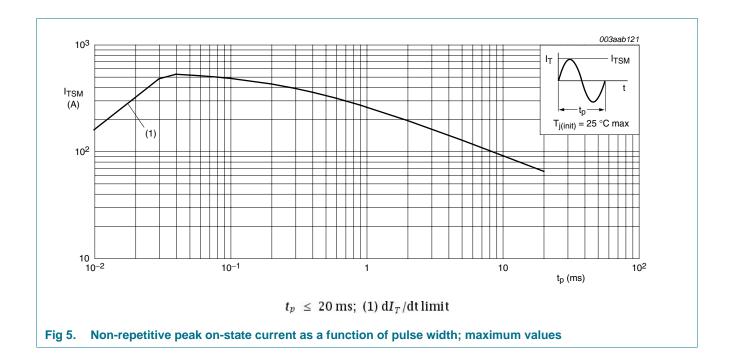


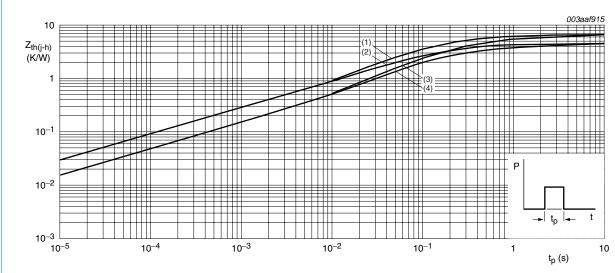
Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; see Figure 6	-	-	4.5	K/W
		full cycle or half cycle; without heatsink compound; see Figure 6	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

6. Isolation characteristics

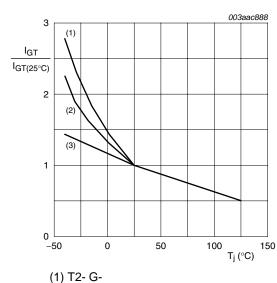
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free ; $50 \text{ Hz} \le f \le 60 \text{ Hz}$; RH $\le 65 \%$; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink ; $f = 1 \text{ MHz}$; $T_h = 25 ^{\circ}\text{C}$	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+; T_j = 25 \text{ °C;}$ see Figure 7	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-; } T_j = 25 ^{\circ}\text{C;}$ see Figure 7	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-; } T_j = 25 \text{ °C;}$ see Figure 7	-	-	10	mA
I _L latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+G+; T_j = 25 \text{ °C;}$ see Figure 8	-	-	12	mA	
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ G-; T_j = 25 \text{ °C;}$ see Figure 8	-	-	18	mA
	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2\text{- G-; } T_j = 25 \text{ °C;}$ see Figure 8	-	-	12	mA	
I _H	holding current	$V_D = 12 \text{ V; } T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } T_j}$	-	-	12	mΑ
V _T	on-state voltage	$I_T = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{\text{ c}}$	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I _D	off-state current	$V_D = 800 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	0.1	0.5	mΑ
Dynamic ch	aracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 110 °C; exponential waveform; gate open circuit	60	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}$; $T_j = 125 ^{\circ}\text{C}$; $I_{T(RMS)} = 8 \text{ A}$; $dV_{com}/dt = 10 \text{V}/\mu\text{s}$; gate open circuit; see Figure 12	5	-	-	A/ms
		$V_D = 400 \text{ V}$; $T_j = 125 \text{ °C}$; $I_{T(RMS)} = 8 \text{ A}$; $dV_{com}/dt = 0.1 \text{ V/}\mu\text{s}$; gate open circuit; see Figure 12	10	-	-	A/ms



- (2) T2+ G-
- (3) T2+ G+

Normalized gate trigger current as a function of Fig 7. junction temperature

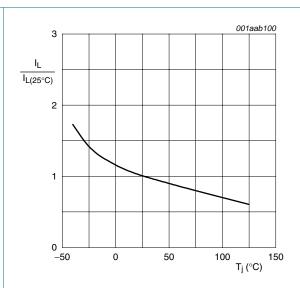
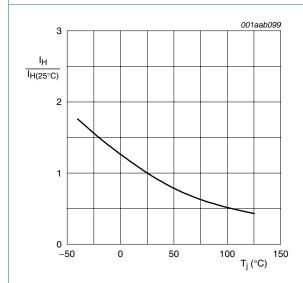
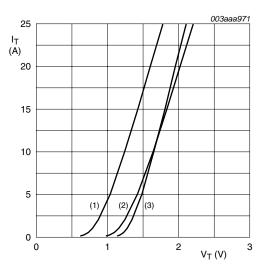


Fig 8. Normalized latching current as a function of junction temperature



Normalized holding current as a function of Fig 9. junction temperature



Vo = 1.264 V; Rs = 0.0378 Ω

(1) Tj = 125 °C; typical values

(2) Tj = 125 °C; maximum values

(3) Tj = 25 °C; maximum values

Fig 10. On-state current as a function of on-state voltage

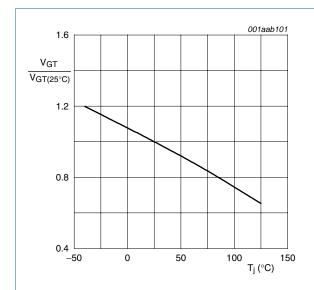


Fig 11. Normalized gate trigger voltage as a function of junction temperature

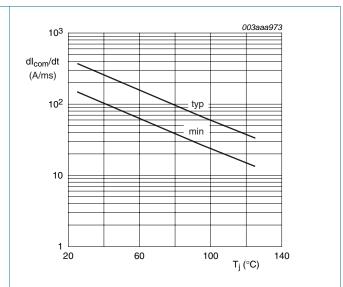
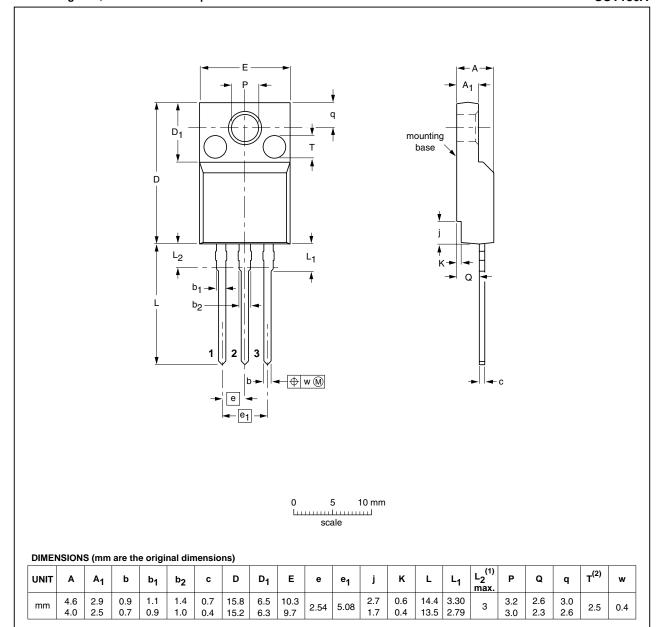


Fig 12. Rate of change of commutating current as a function of junction temperature; typical and minimum values

8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT186A		3-lead TO-220F				-02-04-09 06-02-14

Fig 13. Package outline SOT186A (TO-220F)

BTA208X-800E

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA208X-800E v.7	20110125	Product data sheet	-	BTA208X-800E v.6
Modifications: • Various changes to content.				
BTA208X-800E v.6	20101109	Product data sheet	-	BTA208X_SERIES_D_E_F_5

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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12. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics6
6	Isolation characteristics 6
7	Characteristics7
8	Package outline
9	Revision history11
10	Legal information12
10.1	Data sheet status
10.2	Definitions12
10.3	Disclaimers
10.4	Trademarks13
11	Contact information13

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